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Global Foundries East Fishkill, New York, United States

Title of Change:	Wafer Fab Capacity Expansion for FS3 Trench IGBT 12inch Technology at Global Foundries in New York, US and Gate driver IC 8inch Technology at Maine in South Portland US.			
Proposed First Ship date:	30 Oct 2021 or earlier i	30 Oct 2021 or earlier if approved by customer		
Contact Information:	Contact your local ON S	Contact your local ON Semiconductor Sales Office or <u>Sungdae.Shin@onsemi.com</u>		
PCN Samples Contact:	Sample requests are to Initial PCN or Final PCN Samples delivery timing	Contact your local ON Semiconductor Sales Office or < <u>PCN.samples@onsemi.com</u> >. Sample requests are to be submitted no later than 30 days from the date of first notification, initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <u>Jayoung.Hong@onsemi.com</u>			
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <u>PCN.Support@onsemi.com</u>			
Marking of Parts/ Traceability of Change:	Material will be traceable with ONs lot trace code & tracking			
Change Category:	Wafer Fab Change	Wafer Fab Change		
Change Sub-Category(s):	Manufacturing Site Addition			
Sites Affected:	·			
ON Semiconductor Sites		External Foundry/Subcon Sites		

ON Semiconductor Maine, United States

Description and Purpose:

Qualify 2 different FAB site with 2 different wafer technology as a below table:

The purpose of notification is increase wafer loading capacity.

	FAB Site		
	Before	After	
FS3 TIGBT	ON semiconductor Aizu, Japan ON semiconductor Bucheon, Korea	ON semiconductor Aizu, Japan ON semiconductor Bucheon, Korea Global Foundries East Fishkill, New York, United States	
HDG4DA & HDJ4 gate driver IC	ON semiconductor Bucheon, Korea	ON semiconductor Bucheon, Korea ON Semiconductor Maine, United States	

There are no product material changes as a result of this change.

There is no product marking change as a result of this change.



Reliability Data Summary:

QV DEVICE NAME: FGH75T65SHD-F155, FGH60T65SHD-F155, FGY160T65SPD-F085 RMS: U78532, U78534, U78535, U78536, U76790, U74188, U74191, U72040

PACKAGE: TO247

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta= <u>175</u> °C, <u>100</u> % max rated V	<u>1008</u> hrs	0/ <u>240</u>
HTGB	JESD22-A108	Ta= <u>175</u> °C, <u>100 %</u> max Vge	<u>1008</u> hrs	0/ <u>240</u>
HTSL	JESD22-A103	Ta=175°C, No bias	<u>1008hrs</u>	0/240
TC	JESD22-A104	Ta= - <u>55</u> °C to + <u>150</u> °C	<u>1000</u> сус	0/ <u>240</u>
HAST	JESD22-A110	130°C, 85% RH, 18.8psia, bias	<u>96</u> hrs	0/ <u>240</u>
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	<u>96</u> hrs	0/ <u>240</u>
IOL	ML-STD-750	Ta=25°C, delta Tj=100°C On/Off = 5min	<u>6000cyc</u>	0/240

QV DEVICE NAME: FNB51560TD1, FNA41560T2, FNB80560T3 RMS: U74113, U74114, U74115,

PACKAGE: IPM55, IPM45H, IPM8

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta= <u>150</u> °C, <u>80</u> % max rated V	<u>1008</u> hrs	0/ <u>39</u>
HTSL	JESD22-A103	Ta=150°C, No bias	<u>1008hrs</u>	0/39
TC	JESD22-A104	Ta= - <u>55</u> °C to + <u>150</u> °C	<u>1000</u> сус	0/ <u>69</u>
HAST	JESD22-A110	130°C, 85% RH, 18.8psia, bias	<u>96</u> hrs	0/ <u>45</u>

QV DEVICE NAME: FAN73912MX **RMS 057762** PACKAGE SOICW16

Specification Condition Interval Results Test HTOL JESD22-A108 Ta=125°C, 100 % max rated Vcc 1008 hrs 0/240 HTSL JESD22-A103 Ta= 150°C 2016 hrs 0/240 ΤС JESD22-A104 Ta= -65°C to +150°C 0/240 1000 cyc HAST JESD22-A110 130°C, 85% RH, 18.8psig, bias 192 hrs 0/240 130°C, 85% RH, 18.8psig, unbiased 96 hrs 0/240 uHAST JESD22-A118 J-STD-020 JESD-A113 РС MSL 3 @ 260 °C

QV DEVICE NAME: FSBB10CH120D

RMS K57911 PACKAGE SPM3

Test	Specification	Condition	Interval	Results	
HTSL	JESD22-A103	Ta= 150°C	2016 hrs	0/36	
тс	JESD22-A104	Ta= -40°C to +125°C	1000 cyc	0/66	
THU	JESD22-A101	85°C, 85% RH, unbiased	1008 hrs	0/36	

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Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the <u>PCN Customized Portal</u>.

Part Number	Qualification Vehicle
FNB80460T3	FGY160T65SPD-F085, FNB80560T3, FAN73912MX, FSBB10CH120D
FNB80560T3	FGY160T65SPD-F085, FNB80560T3, FAN73912MX, FSBB10CH120D
FNB81060T3	FGY160T65SPD-F085, FNB80560T3, FAN73912MX, FSBB10CH120D



Appendix A: Changed Products

Product	Customer Part Number	Qualification Vehicle	New Part Number	Replacement Supplier
FNB80560T3		FGY160T65SPD-F085, FNB80560T3, FAN73912MX, FSBB10CH120D		
FNB81060T3		FGY160T65SPD-F085, FNB80560T3, FAN73912MX, FSBB10CH120D		